

# Agilent MSA-0420 Cascadable Silicon Bipolar MMIC Amplifier

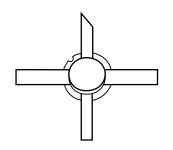
Data Sheet

## **Description**

The MSA-0420 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a hermetic, high reliability package. This MMIC is designed for use as a general purpose  $50~\Omega$  gain block. Typical applications include narrow and broad band IF and RF amplifiers in industrial and military applications.

The MSA-series is fabricated using Agilent's 10 GHz f<sub>T</sub>, 25 GHz f<sub>MAX</sub>, silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

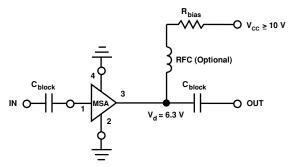
## 200 mil BeO Package



#### **Features**

- Cascadable 50  $\Omega$  Gain Block
- 3 dB Bandwidth: DC to 4.0 GHz
- 8.5 dB Typical Gain at 1.0 GHz
- 16.0 dBm Typical  $P_{1 dB}$  at 1.0 GHz
- Unconditionally Stable (k>1)
- Hermetic Metal/Beryllia Microstrip Package

### **Typical Biasing Configuration**



## MSA-0420 Absolute Maximum Ratings

Parameter	Absolute Maximum <sup>[1]</sup>
Device Current	120 mA
Power Dissipation <sup>[2,3]</sup>	850 mW
RF Input Power	+13 dBm
Junction Temperature	200°C
Storage Temperature	−65 to 200°C

Thermal Resistance $[2,4]$ :					
$\theta_{jc} = 40^{\circ} \text{C/W}$					

### **Notes:**

- 1. Permanent damage may occur if any of these limits are exceeded.

- T<sub>CASE</sub> = 25°C.
   Derate at 25 mW/°C for T<sub>C</sub> > 166°C.
   The small spot size of this technique results in a higher, though more accurate determination of  $q_{jc}\, than \ do \ alternate \ methods.$

## Electrical Specifications<sup>[1]</sup>, $T_A = 25^{\circ}C$

Symbol	<b>Parameters and Test Conditions:</b>	Units	Min.	Тур.	Max.	
GP	Power Gain ( S <sub>21</sub>   <sup>2</sup> )	f = 0.1 GHz	dB	7.5	8.5	9.5
$\Delta G_{ m P}$	Gain Flatness	f = 0.1  to  2.5  GHz	dB		±0.6	±1.0
f <sub>3 dB</sub>	3 dB Bandwidth		GHz		4.3	
VSWR	Input VSWR	f = 0.1 to 2.5 GHz			1.7:1	
VSWIL	Output VSWR	f = 0.1 to 2.5 GHz			1.8:1	
NF	$50~\Omega$ Noise Figure	f = 1.0 GHz	dB		6.5	
P <sub>1 dB</sub>	Output Power at 1 dB Gain Compression	f = 1.0  GHz	dBm	14.0	16.0	
$IP_3$	Third Order Intercept Point	f = 1.0  GHz	dBm		30.0	
$t_{\mathrm{D}}$	Group Delay	f = 1.0  GHz	psec		140	
$V_{d}$	Device Voltage		V	5.7	6.3	6.9
dV/dT	Device Voltage Temperature Coefficient		mV/°C		-8.0	

#### Note:

1. The recommended operating current range for this device is 40 to 110 mA. Typical performance as a function of current is on the following page.

MSA-0420 Typical Scattering Parameters	$(\mathbf{Z}_0 = 5)$	$0 \Omega, \mathbf{T}_{A}$	$_{\rm a} = 25^{\circ}{\rm C},  {\rm I}_{\rm d} = 90  {\rm m}$	A)
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Freq.	$\mathbf{S}_{11}$			$\mathbf{S}_{21}$ $\mathbf{S}_{12}$		$\mathbf{S}_{21}$			$\mathbf{S}_2$	22
GHz	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang
0.1	.25	177	8.6	2.70	175	-16.4	.151	1	.03	-30
0.2	.25	173	8.6	2.69	170	-16.5	.150	1	.04	-59
0.4	.24	167	8.6	2.69	159	-16.5	.150	-1	.07	-79
0.6	.22	160	8.5	2.67	149	-16.4	.152	-2	.10	-92
0.8	.21	154	8.5	2.66	139	-16.3	.154	-2	.13	-99
1.0	.20	148	8.3	2.60	129	-16.1	.156	-3	.16	-109
1.5	.14	136	8.1	2.54	104	-15.6	.166	-4	.22	-124
2.0	.10	136	7.9	2.48	80	-14.8	.181	-6	.25	-139
2.5	.08	161	7.4	2.34	62	-14.3	.193	-5	.28	-147
3.0	.10	178	7.0	2.24	39	-13.7	.206	-11	.31	-157
3.5	.13	176	6.6	2.13	18	-12.6	.233	-18	.34	-167
4.0	.14	163	5.9	1.97	-3	-11.9	.253	-25	.36	-176
4.5	.14	133	5.3	1.83	-23	-11.3	.273	-33	.37	174
5.0	.16	91	4.5	1.69	-343	-10.5	.299	-43	.37	162

## Typical Performance, $T_A = 25^{\circ}C$

(unless otherwise noted)

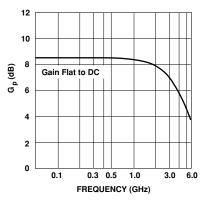


Figure 1. Typical Power Gain vs. Frequency,  $T_A$  = 25°C,  $I_d$  = 90 mA.

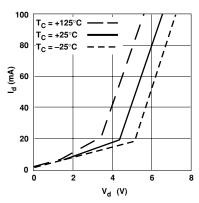


Figure 2. Device Current vs. Voltage.

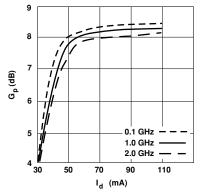


Figure 3. Power Gain vs. Current.

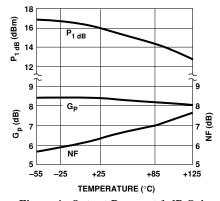


Figure 4. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Case Temperature, f = 1.0 GHz,  $I_d$  = 90 mA.

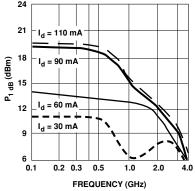


Figure 5. Output Power at 1 dB Gain Compression vs. Frequency.

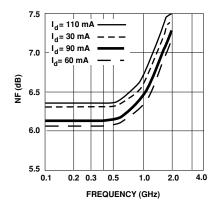
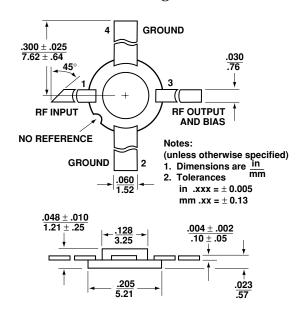


Figure 6. Noise Figure vs. Frequency.

## **Ordering Information**

Part Numbers	No. of Devices	Comments		
MSA-0420	10	Bulk		

### 200 mil BeO Package Dimensions



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Obsoletes 5965-9574E

Data subject to change.

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